

67. (NEW) The method of claim 56 further comprising the step of:
flowing a temperature control fluid through passages disposed in a platen
having the polishing material disposed thereon.

68. (NEW) The method of claim 67, wherein the step of flowing the
temperature control fluid through the platen further comprises the step of:
reducing the temperature of the polishing material.

REMARKS

This reply is intended as a full and complete response to the Office Action
mailed on October 25, 2001, (paper no. 7).

REJECTIONS

35 U.S.C. §112

Claims 16 and 19

Claims 16 and 19 stand rejected under 35 U.S.C. §112, second
paragraph, for not providing antecedent basis for the term "polishing media". In
response, the Applicants have amended claims 16 and 19 to depend from claim
18 and have replaced the term "polishing media" with "polishing material".
Antecedent basis for the term "polishing material" is provided in base claim 18.
Accordingly, the Applicants respectfully request the rejection of claims 16 and 19
be withdrawn.

35 U.S.C. §102(b)

Claims 13-15, 17, 24 and 27

Claims 13-15, 17, 24 and 27 stand rejected as being anticipated by United
States Patent No. 5,749,769, issued May 12, 1998 to Church et al., (hereinafter
referred to as "Church"). In response, the Applicants have cancelled claim 13
and re-written claim 18 in independent form, incorporating the limitations of claim

13. The Examiner, in his Office Action of October 25, 2001, has indicated that claim 18 is allowable in this form.

As claims 15-27 all depend from claim 18, these claims are also allowable over Church. Accordingly, the Applicants request the rejection to claims 14-15, 17, 24 and 27 be withdrawn.

35 U.S.C. §103

Claims 25 and 26

Claims 25 and 26 stand rejected as being unpatentable over Church in view of United States Patent No. 5,718,620, issued February 17, 1998 to Tanaka et al., (hereinafter referred to as "Tanaka"). In response, the Applicants have amended claim 25 to depend from claim 18.

As discussed above, the Examiner has indicated that claim 18 is allowable in independent form. Therefore, claims 25 and 26, which depend from claim 18, are also allowable over Church in view of Tanaka. Accordingly, the Applicants request the rejection to claims 25 and 26 be withdrawn.

35 U.S.C. §103

Claim 16

Claim 16 stands rejected as being unpatentable over Church in view of United States Patent No. 5,647,789, issued July 15, 1997 to Kitta et al., (hereinafter referred to as "Kitta"). In response, the Applicants have amended claim 16 to depend from claim 18.

As discussed above, the Examiner has indicated that claim 18 is allowable in independent. Therefore, claim 16, which depends from claim 18, is also allowable over Church in view of Kitta. Accordingly, the Applicants request the rejection to claim 16 be withdrawn.

ALLOWABLE SUBJECT MATTER

The Applicants thank the Examiner for his comments regarding the allowability of claims 18 and 20-23 if re-written as independent form to include the limitations of all intervening claims and the allowability of claim 19 as re-written to overcome the rejection under 35 U.S.C. §112 discussed above. The Applicants have amended claim 18 as suggested. New claims 43 and 56 have been added reciting the limitations of claims 19 and 20 in independent form as suggested.

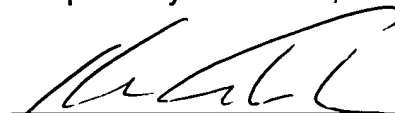
CONCLUSION

Thus, the Applicants submit that none of the claims presently in the application are anticipated or unpatentable in light of the references of record. Consequently, the Applicants believe that all these claims are presently in condition for allowance. Accordingly, both reconsideration of this application and its swift passage to issue are earnestly solicited.

If, however, the Examiner believes that there are any unresolved issues, it is requested that the Examiner telephone Mr. Keith Taboada at (732) 530-9404 so that appropriate arrangements can be made for resolving such issues as expeditiously as possible.

Respectfully submitted,

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APPENDIX I
MARK-UP OF AMENDED CLAIMS

1. (CANCELLED) A system for processing substrates comprising:
a polishing head adapted to retain a substrate during processing; and
a polishing material disposed below the polishing head, the polishing material movable relative to the polishing head in a first direction and in a second direction different from the first direction.
2. (CANCELLED) The system of claim 1, wherein the polishing material moves in the first direction when polishing one substrate and in the second direction when polishing another substrate.
3. (CANCELLED) The system of claim 1, wherein the polishing material rotates to define the first direction.
4. (CANCELLED) The system of claim 1, wherein the polishing material rotates and the polishing head provides other motion which together define the first direction.
5. (CANCELLED) The system of claim 1, wherein the polishing head is moved linearly in one or more directions to define the first direction.
6. (CANCELLED) The system of claim 1, wherein the polishing material is moved linearly to define the first direction.
7. (CANCELLED) The system of claim 1 further comprising:
a platen supporting the polishing material.

8. (CANCELLED) The system of claim 7, wherein the platen further comprises:

- a top surface that supports the polishing material; and
- a plurality of passages disposed in the platen, the passages adapted to flow a temperature control fluid.

9. (CANCELLED) The system of claim 1, wherein the polishing material is disposed on a chemical mechanical polisher.

10. (CANCELLED) A system for processing substrates comprising:

- a polishing material;
- at least one rotatable platen supporting the polishing material, the rotational direction of the platen reversed at least once between processing at least two substrates; and
- at least one polishing head disposed above the platen, the polishing head adapted to retain a substrate during processing.

11. (CANCELLED) The system of claim 10 further comprising:

- a carousel supporting the polishing head.

12. (CANCELLED) The system of claim 10, wherein the platen further comprises:

- a top surface that supports the polishing material; and
- a plurality of passages disposed in the platen, the passages adapted to flow a temperature control fluid.

13. (CANCELLED) A method for processing substrates comprising the steps of:

- providing a first relative motion between at least one substrate and a polishing material; and

providing a second relative motion between at least another substrate and the polishing material.

14. (AMENDED) The method of claim 18 [13], wherein the step of providing the first relative motion further comprises the step of:

performing a chemical mechanical planarization process.

15. (AMENDED) The method of claim 18 [13], wherein the step of providing the first relative motion further comprises the step of:

rotating a platen supporting the polishing material.

16. (AMENDED) The method of claim 18 [13], wherein the step of providing the second relative motion further comprises the step of:

rotating a platen supporting the polishing material [media] in a direction opposite a rotational direction of the first relative motion.

17. (AMENDED) The method of claim 18 [13], wherein the step of providing the first relative motion further comprises the step of:

moving a polishing head retaining the first substrate.

18. (AMENDED) [The method of claim 13, wherein the step of providing the first relative motion further comprises the step of:] A method for processing substrates comprising the steps of:

providing a first relative motion between at least one substrate and a polishing material by moving the polishing head in a planar motion; and

providing a second relative motion between at least another substrate and the polishing material.

19. (AMENDED) The method of claim 18 [13], wherein the step of providing the first relative motion further comprises the step of:

moving the polishing material [media] in a linear direction.

20. (AMENDED) The method of claim 18 [13], wherein the step of providing the first relative motion further comprises the step of:

processing additional substrates utilizing the first relative motion between the at least one substrates and the polishing material before providing the second relative motion between the at least another substrate and the polishing material.

23. (AMENDED) The method of claim 18 [13], wherein the first relative motion is opposite the second relative motion.

24. (AMENDED) The method of claim 18 [13] further comprising the step of:
processing a third substrate utilizing the first relative motion.

25. (AMENDED) The method of claim 18 [13] further comprising the step of:
flowing a temperature control fluid through passages disposed in a platen having the polishing material disposed thereon.

27. (CANCELLED) A method for processing a substrate comprising the steps of:

providing a first relative motion between a substrate and a polishing material during at least a portion of a polishing cycle; and

providing a second relative motion between the substrate and the polishing material during at least another portion of the polishing cycle.

28. (CANCELLED) A computer-readable medium having stored thereon a plurality of instructions, the plurality of instructions including instructions which, when executed by a processor, cause a semiconductor processing system to perform the steps of:

providing a first relative motion between at least one substrate and a polishing material; and

providing a second relative motion between at least another substrate and the polishing material.

29. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the first relative motion further comprises the step of:

performing a chemical mechanical planarization process.

30. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the first relative motion further comprises the step of:

rotating a platen supporting the polishing material.

31. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the second relative motion further comprises the step of:

rotating a platen supporting the polishing media in a direction opposite a rotational direction of the first relative motion.

32. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the first relative motion further comprises the step of:

moving a polishing head retaining the first substrate.

33. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the first relative motion further comprises the step of:

moving the polishing head in a planar motion.

34. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the first relative motion further comprises the step of:

moving the polishing media in a linear direction.

35. (CANCELLED) The computer-readable medium of claim 28, wherein the step of providing the first relative motion further comprises the step of:

processing additional substrates utilizing the first relative motion between the at least one substrates and the polishing material before providing the second relative motion between the at least another substrate and the polishing material.

36. (CANCELLED) The computer-readable medium of claim 35, wherein the step of providing the second relative motion further comprises the step of:

processing additional substrates utilizing the second relative motion between the at least another substrate and the polishing material.

37. (CANCELLED) The computer-readable medium of claim 35 further comprising the step of:

processing another batch of substrates utilizing the first relative motion between the substrates and the polishing material.

38. (CANCELLED) The computer-readable medium of claim 28, wherein the first relative motion is in a direction opposite the second relative motion.

39. (CANCELLED) The computer-readable medium of claim 28 further comprising:

processing a third substrate utilizing the first relative motion.

40. (CANCELLED) The computer-readable medium of claim 28 further comprising:

flowing a temperature control fluid through passages disposed in a platen having the polishing material disposed thereon.

41. (CANCELLED) The computer-readable medium of claim 40, wherein the step of flowing the temperature control fluid through the platen further comprises the step of:

reducing the temperature of the polishing material.

42. (CANCELLED) A computer-readable medium having stored thereon a plurality of instructions, the plurality of instructions including instructions which, when executed by a processor, cause a semiconductor processing system to perform the steps of:

providing a first relative motion between a substrate and a polishing material during at least a portion of a polishing cycle; and

providing a second relative motion between the substrate and the polishing material during at least another portion of the polishing cycle.

43. (NEW) A method for processing substrates comprising the steps of:

providing a first relative motion between at least one substrate and a polishing material by moving the polishing material in a linear direction; and

providing a second relative motion between at least another substrate and the polishing material.

44. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:

performing a chemical mechanical planarization process.

45. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:

rotating a platen supporting the polishing material.

46. (NEW) The method of claim 43, wherein the step of providing the second relative motion further comprises the step of:

rotating a platen supporting the polishing material in a direction opposite a rotational direction of the first relative motion.

47. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:

moving a polishing head retaining the first substrate.

48. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:

moving the polishing head in a planar motion.

49. (NEW) The method of claim 43, wherein the step of providing the first relative motion further comprises the step of:

processing additional substrates utilizing the first relative motion between the at least one substrates and the polishing material before providing the second relative motion between the at least another substrate and the polishing material.

50. (NEW) The method of claim 49, wherein the step of providing the second relative motion further comprises the step of:

processing additional substrates utilizing the second relative motion between the at least another substrate and the polishing material.

51. (NEW) The method of claim 49 further comprising the step of:

processing another batch of substrates utilizing the first relative motion between the substrates and the polishing material.

52. (NEW) The method of claim 43, wherein the first relative motion is opposite the second relative motion.

53. (NEW) The method of claim 43 further comprising the step of:
processing a third substrate utilizing the first relative motion.
54. (NEW) The method of claim 43 further comprising the step of:
flowing a temperature control fluid through passages disposed in a platen
having the polishing material disposed thereon.
55. (NEW) The method of claim 54, wherein the step of flowing the
temperature control fluid through the platen further comprises the step of:
reducing the temperature of the polishing material.
56. (NEW) A method for processing substrates comprising the steps of:
providing a first relative motion between at least one substrate and a
polishing material;
providing a second relative motion between at least another substrate and
the polishing material; and
processing additional substrates utilizing the first relative motion between
the at least one substrates and the polishing material before providing the
second relative motion between the at least another substrate and the polishing
material.
57. (NEW) The method of claim 56, wherein the step of providing the first
relative motion further comprises the step of:
performing a chemical mechanical planarization process.
58. (NEW) The method of claim 56, wherein the step of providing the first
relative motion further comprises the step of:
rotating a platen supporting the polishing material.

59. (NEW) The method of claim 56, wherein the step of providing the second relative motion further comprises the step of:

rotating a platen supporting the polishing material in a direction opposite a rotational direction of the first relative motion.

60. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:

moving a polishing head retaining the first substrate.

61. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:

moving the polishing head in a planar motion.

62. (NEW) The method of claim 56, wherein the step of providing the first relative motion further comprises the step of:

moving the polishing material in a linear direction.

63. (NEW) The method of claim 62, wherein the step of providing the second relative motion further comprises the step of:

processing additional substrates utilizing the second relative motion between the at least another substrate and the polishing material.

64. (NEW) The method of claim 62 further comprising the step of:

processing another batch of substrates utilizing the first relative motion between the substrates and the polishing material.

65. (NEW) The method of claim 56, wherein the first relative motion is opposite the second relative motion.

66. (NEW) The method of claim 56 further comprising the step of:
processing a third substrate utilizing the first relative motion.
67. (NEW) The method of claim 56 further comprising the step of:
flowing a temperature control fluid through passages disposed in a platen
having the polishing material disposed thereon.
68. (NEW) The method of claim 67, wherein the step of flowing the
temperature control fluid through the platen further comprises the step of:
reducing the temperature of the polishing material.